

2 W Low-Cost Packaged PHEMT GaAs Power FETs

FEATURES

- 2 W Typical Output Power at 6 GHz
- 9 dB Typical Linear Power Gain at 6 GHz
- High Linearity: IP3 = 43 dBm Typical at 6 GHz
- High Power Added Efficiency: Nominal PAE of 43 % at 6 GHz
- Suitable for High Reliability Application
- Breakdown Voltage: $BV_{DGO} \geq 18$ V
- $L_g = 0.6$ μ m, $W_g = 5$ mm
- Tight V_p ranges control
- High RF input power handling capability
- 100 % DC Tested
- Low Cost Ceramic Package

PHOTO ENLARGEMENT



DESCRIPTION

The TC2676 is packaged with the TC1606 Pseudomorphic High Electron Mobility Transistor (PHEMT) chip.

The Cu-based ceramic package provides excellent thermal conductivity for the GaAs FET. All devices are 100% DC tested to assure consistent quality. Typical applications include high dynamic range power amplifiers for commercial and military high performance power applications.

ELECTRICAL SPECIFICATIONS ($T_A=25$ °C)

Symbol	Conditions	MIN	TYP	MAX	UNIT
P_{1dB}	Output Power at 1dB Gain Compression Point, $f = 6$ GHz $V_{DS} = 8$ V, $I_{DS} = 500$ mA	32.5	33		dBm
G_L	Linear Power Gain, $f = 6$ GHz $V_{DS} = 8$ V, $I_{DS} = 500$ mA		9		dB
IP3	Intercept Point of the 3 rd -order Intermodulation, $f = 6$ GHz $V_{DS} = 8$ V, $I_{DS} = 500$ mA, * $P_{SCL} = 20$ dBm		43		dBm
PAE	Power Added Efficiency at 1dB Compression Power, $f = 6$ GHz		43		%
I_{DSS}	Saturated Drain-Source Current at $V_{DS} = 2$ V, $V_{GS} = 0$ V		1.25		A
g_m	Transconductance at $V_{DS} = 2$ V, $V_{GS} = 0$ V		850		mS
V_p	Pinch-off Voltage at $V_{DS} = 2$ V, $I_D = 10$ mA		-1.7**		Volts
BV_{DGO}	Drain-Gate Breakdown Voltage at $I_{DGO} = 2.5$ mA	18	22		Volts
R_{th}	Thermal Resistance		8		°C/W

* P_{SCL} : Output Power of Single Carrier Level

** For the tight control of the pinch-off voltage range, we divide TC2676 into 3 model numbers to fit customer design requirement
 (1)TC2676P1519 : $V_p = -1.5$ V to -1.9 V (2)TC2676P1620 : $V_p = -1.6$ V to -2.0 V (3)TC2676P1721 : $V_p = -1.7$ V to -2.1 V If
 required, customer can specify the requirement in purchasing document. For special V_p requirement, please contact factory for details.

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$) RECOMMENDED OPERATING CONDITION

Symbol	Parameter	Rating
V_{DS}	Drain-Source Voltage	12 V
V_{GS}	Gate-Source Voltage	-5 V
I_{DS}	Drain Current	I_{DSS}
P_{in}	RF Input Power, CW	30 dBm
P_T	Continuous Dissipation	7.7 W
T_{CH}	Channel Temperature	175 $^\circ\text{C}$
T_{STG}	Storage Temperature	- 65 $^\circ\text{C}$ to +175 $^\circ\text{C}$

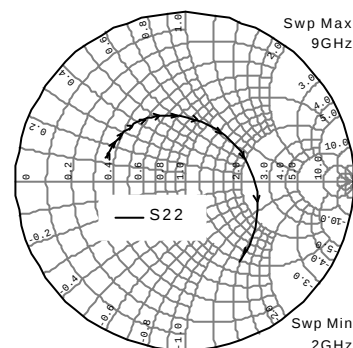
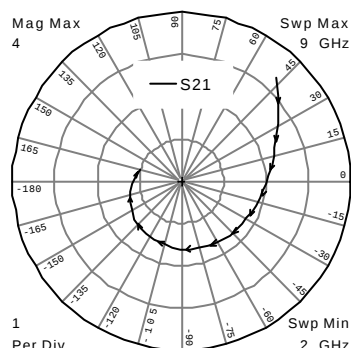
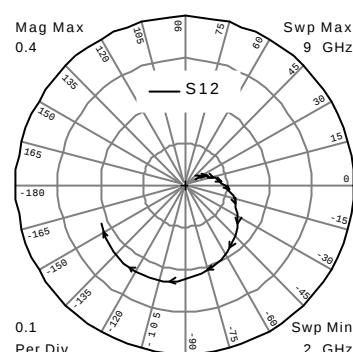
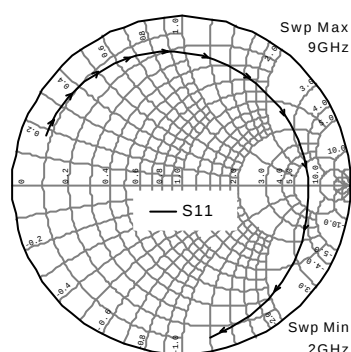
Symbol	Parameter	Rating
V_{DS}	Drain to Source Voltage	8 V
I_D	Drain Current	500 mA

HANDLING PRECAUTIONS:

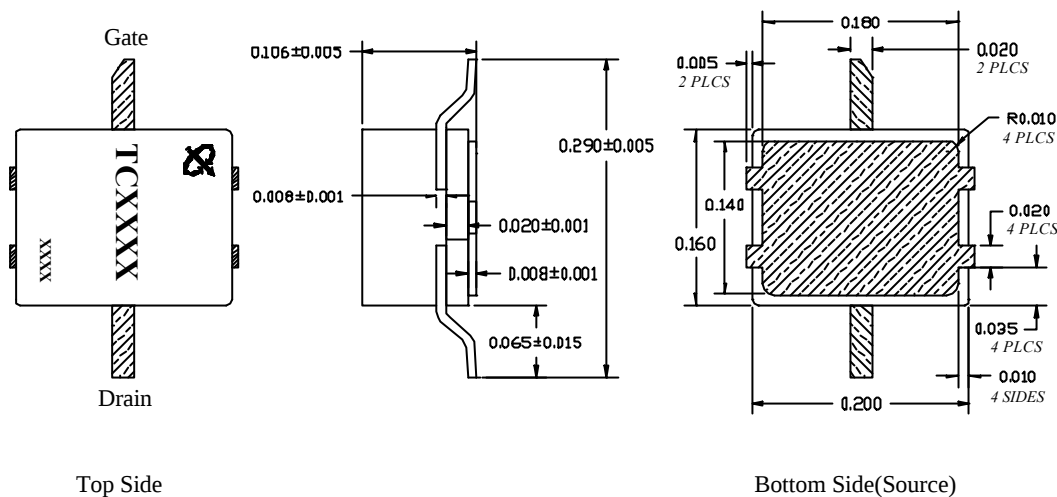
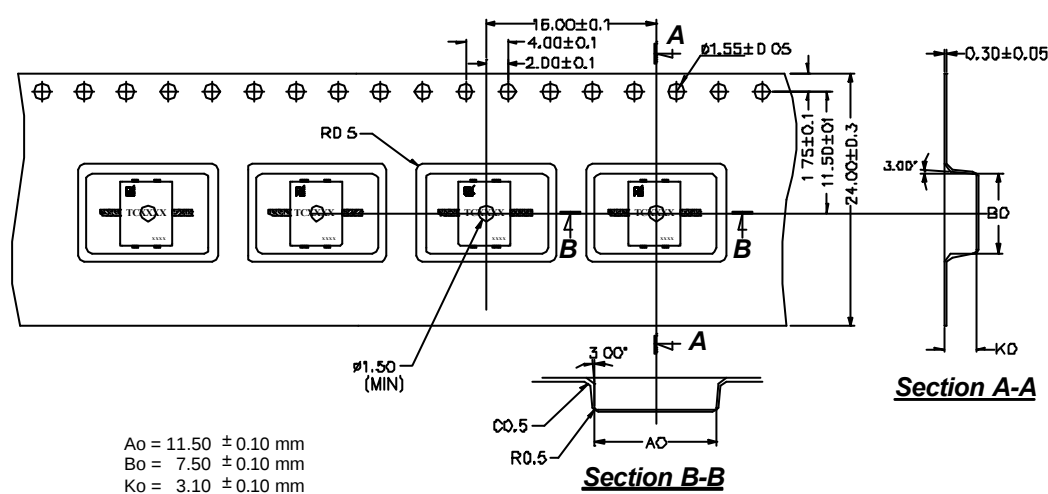
The user must operate in a clean, dry environment. Electrostatic Discharge (ESD) precautions should be observed at all stages of storage, handling, assembly, and testing. The static discharge must be less than 300V.

TYPICAL SCATTERING PARAMETERS ($T_A=25^\circ\text{C}$)

$V_{DS} = 8\text{ V}$, $I_{DS} = 500\text{ mA}$



FREQUENCY (GHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
2	0.8583	159.78	3.3298	47.16	0.0396	28.75	0.4800	163.15
3	0.8419	137.46	2.3730	20.35	0.0580	20.43	0.4735	149.56
4	0.8171	114.30	1.9527	-6.75	0.0832	6.31	0.4560	134.61
5	0.7833	87.34	1.7538	-35.79	0.1169	-13.20	0.4254	116.87
6	0.7492	53.95	1.6530	-68.43	0.1597	-38.78	0.3866	93.67
7	0.7445	12.53	1.5564	-106.23	0.2058	-71.41	0.3603	58.23
8	0.8082	-34.29	1.3586	-149.76	0.2347	-111.25	0.4064	3.35
9	0.9125	-79.43	1.0009	164.08	0.2175	-154.91	0.5776	-56.08

OUTLINE DIMENSIONS (Unit: inch)

TAPE & REEL PACKAGE ORIENTATION (Unit: mm)


Standard Reel Size	7"
Standard Reel Quantity	400